

L Number	Hits	Search Text	DB	Time stamp
1	6	semiconductor and (transducer with resonator) and (electrode\$1 with (al or aluminum or aluminium or Ti or titanium)) and (substrate with (silicon or si or GaAs or gallium)) and (piezoelectric with ("AlN.sub.3" or (aluminum adj nitride) or ZnO or (zinc adj oxide)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/17 16:25
-	5884	semiconductor and piezoelectric and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 09:47
-	2657	(semiconductor and piezoelectric and electrode) and (thin with film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/09 15:46
-	2	((semiconductor and piezoelectric and electrode) and (thin with film)) and (CMP and reflow and (lift with off))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/09 15:51
-	29	((semiconductor and piezoelectric and electrode) and (thin with film)) and (CMP or reflow or (lift with off)) and (stress with reduc\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/09 16:02
-	0	(semiconductor and piezoelectric and electrode) and (burried with electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/09 16:02
-	72	(semiconductor and piezoelectric and electrode) and (buried with electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/09 16:02
-	5884	semiconductor and piezoelectric and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/10 10:01
-	206	(semiconductor and piezoelectric and electrode) and flush	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/11 11:45
-	206	(semiconductor and piezoelectric and electrode) and flush	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/11 13:23
-	2435	(semiconductor and piezoelectric and electrode) and (thin adj film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/11 13:41
-	75	((semiconductor and piezoelectric and electrode) and (thin adj film)) and planarization	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/11 15:03
-	15	semiconductor and (thin with film with resonator) and CMP	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/11 15:45

-	103	semiconductor and (thin with film with resonator) and planar\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/11 15:45
-	574	resonator and piezoelectric and electrode and (planar or planarized or planarization)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 09:47
-	412	(resonator and piezoelectric and electrode and (planar or planarized or planarization)) and thin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 09:47
-	249	(resonator and piezoelectric and electrode and (planar or planarized or planarization)) and (thin adj film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 13:11
-	1257	semiconductor and piezoelectric and (thin with film) and electrode and ((silicon adj oxide) or "SiO.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 13:15
-	770	(semiconductor and piezoelectric and (thin with film) and electrode and ((silicon adj oxide) or "SiO.sub.2")) and (planar\$4 or flat)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 13:13
-	7	semiconductor and (piezoelectric with ((planar or flat) adj surface)) and (thin with film) and electrode and ((silicon adj oxide) or "SiO.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 13:23
-	12	semiconductor and (piezoelectric with ((planar or flat) adj surface)) and electrode and ((silicon adj oxide) or "SiO.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 13:29
-	5	(semiconductor and (piezoelectric with ((planar or flat) adj surface)) and electrode and ((silicon adj oxide) or "SiO.sub.2")) not (semiconductor and (piezoelectric with ((planar or flat) adj surface)) and (thin with film) and electrode and ((silicon adj oxide) or "SiO.sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 13:28
-	3	semiconductor and (((aluminum adj nitride) or "AlN.sub.3" or (zinc adj oxide)) with ((planar or flat) adj surface)) and electrode and ((silicon adj oxide) or "SiO.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 13:34
-	537	semiconductor and (piezo) and electrode and ((silicon adj oxide) or "SiO.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 14:46
-	11	"781820"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 14:57
-	2	("5410208").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:05

	2	("5898348").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:07
	4	(("6377135") or ("6351055")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:10
	4	(("5608362") or ("5350965")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:40
	351	semiconductor and (buried adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:41
	11	(semiconductor and (buried adj electrode)) and piezoelectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:45
	27	(semiconductor and (buried adj electrode)) and planarization	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:49
	1	((semiconductor and (buried adj electrode)) and planarization) and (piezoelectric or "AlN. ₃ " or "ZnO")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:50
	1451	semiconductor and transducer\$1 and electrode and planar\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 16:18
	634	(semiconductor and transducer\$1 and electrode and planar\$4) and piezoelectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 16:19
	527	((semiconductor and transducer\$1 and electrode and planar\$4) and piezoelectric) and ((silicon adj oxide) or "SiO. ₂ ")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 16:19
	13	((semiconductor and transducer\$1 and electrode and planar\$4) and piezoelectric) and ((silicon adj oxide) or "SiO. ₂ ") and cmp	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 16:22
	2	((semiconductor and transducer\$1 and electrode and planar\$4) and piezoelectric) and ((silicon adj oxide) or "SiO. ₂ ") and (piezoelectric with defects)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 16:29
	83	(381/353).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 16:31
	186	(piezoelectric with film) and (patterned with electrode) and dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 10:17

-	20	("3582691" "4054808" "4240002" "4363991" "4461179" "4578611" "4611141" "4651310" "4680595" "4732351" "4761582" "4849668" "4857887" "4864179" "4914565" "5305507" "5315203" "5415175" "5438998" "5493541"). PN.	USPAT	2003/09/16 10:12
-	16	5656882.URPN.	USPAT	2003/09/16 10:12
-	25	("3582691" "4054808" "4240002" "4363991" "4458173" "4461179" "4578611" "4611141" "4651310" "4680595" "4732351" "4742264" "4761582" "4849668" "4857887" "4864179" "4914565" "5305507" "5315203" "5404067" "5415175" "5438998" "5493541" "5632841" "5656882"). PN.	USPAT	2003/09/16 10:15
-	3	6069433.URPN.	USPAT	2003/09/16 10:16
-	359	(piezoelectric) and (thin adj film) and (patterned with electrode) and dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/16 10:17
-	186	(piezoelectric with film) and (patterned with electrode) and dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/16 12:00
-	194	((piezoelectric) and (thin adj film) and (patterned with electrode) and dielectric) not ((piezoelectric with film) and (patterned with electrode) and dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/16 12:00
-	20	((aluminum adj nitride) or "AlN.sub.3" or (zinc adj oxide) or "ZnO") same (thin adj film) and ((patterned adj electrode\$1) same dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/16 11:43
-	1	((aluminium adj nitride) or "AlN.sub.3" or (zinc adj oxide) or "ZnO") same (thin adj film) and ((patterned adj electrode\$1) same dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/16 11:43
-	2346	barber.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/16 11:43
-	36	barber.in. and piezoelectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/16 11:50
-	3	piezoelectric same (weakening adj effect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/16 11:51
-	222	piezoelectric same (internal adj stress)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/16 12:00
-	4	(piezoelectric same (internal adj stress)) and (patterned adj electrode\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/16 11:55

-	0	piezoelectric and ((patterned adj electrode\$1) same (dielectric adj sidewalls))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 11:55
-	0	piezoelectric and ((patterned adj electrode\$1) same (dielectric with side))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 11:56
-	0	piezoelectric and ((patterned adj electrode\$1) same (dielectric with spacers))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 11:56
-	25	piezoelectric and ((patterned adj electrode\$1) same (dielectric with layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 11:57
-	1790	piezoelectric with membrane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 11:58
-	31	(piezoelectric with membrane) and (patterned adj electrode\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 12:01
-	805	(piezoelectric with membrane) and (electrode\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 11:59
-	774	((piezoelectric with membrane) and (electrode\$1)) not ((piezoelectric with membrane) and (patterned adj electrode\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 12:00
-	774	((((piezoelectric with membrane) and (electrode\$1)) not ((piezoelectric with membrane) and (patterned adj electrode\$1))) not (piezoelectric and ((patterned adj electrode\$1) same (dielectric with layer))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 12:00
-	774	((((piezoelectric with membrane) and (electrode\$1)) not ((piezoelectric with membrane) and (patterned adj electrode\$1))) not (piezoelectric and ((patterned adj electrode\$1) same (dielectric with layer)))) not (("3582691" "4054808" "4240002" "4363991" "4461179" "4578611" "4611141" "4651310" "4680595" "4732351" "4761582" "4849668" "4857887" "4864179" "4914565" "5305507" "5315203" "5415175" "5438998" "5493541").PN.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 12:00

-	772	(((((piezoelectric with membrane) and (electrode\$1)) not ((piezoelectric with membrane) and (patterned adj electrode\$1))) not (piezoelectric and ((patterned adj electrode\$1) same (dielectric with layer)))) not ((("3582691" "4054808" "4240002" "4363991" "4461179" "4578611" "4611141" "4651310" "4680595" "4732351" "4761582" "4849668" "4857887" "4864179" "4914565" "5305507" "5315203" "5415175" "5438998" "5493541").PN.)) not (((piezoelectric) and (thin adj film) and (patterned with electrode) and dielectric) not ((piezoelectric with film) and (patterned with electrode) and dielectric))	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 12:00
-	750	(((((piezoelectric with membrane) and (electrode\$1)) not ((piezoelectric with membrane) and (patterned adj electrode\$1))) not (piezoelectric and ((patterned adj electrode\$1) same (dielectric with layer)))) not ((("3582691" "4054808" "4240002" "4363991" "4461179" "4578611" "4611141" "4651310" "4680595" "4732351" "4761582" "4849668" "4857887" "4864179" "4914565" "5305507" "5315203" "5415175" "5438998" "5493541").PN.)) not (((piezoelectric) and (thin adj film) and (patterned with electrode) and dielectric) not ((piezoelectric with film) and (patterned with electrode) and dielectric)) not ((piezoelectric with film) and (patterned with electrode) and dielectric)	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 12:01
-	179	(((((piezoelectric with membrane) and (electrode\$1)) not ((piezoelectric with membrane) and (patterned adj electrode\$1))) not (piezoelectric and ((patterned adj electrode\$1) same (dielectric with layer)))) not ((("3582691" "4054808" "4240002" "4363991" "4461179" "4578611" "4611141" "4651310" "4680595" "4732351" "4761582" "4849668" "4857887" "4864179" "4914565" "5305507" "5315203" "5415175" "5438998" "5493541").PN.)) not (((piezoelectric) and (thin adj film) and (patterned with electrode) and dielectric) not ((piezoelectric with film) and (patterned with electrode) and dielectric)) not ((piezoelectric with film) and (patterned with electrode) and dielectric)) and semiconductor	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 12:01
-	218	semiconductor and (lower with thickness with electrode\$1) and piezoelectric	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/17 10:20
-	18	semiconductor and ((reduce or reduced or reducing or thinning or thinned) with lower with thickness with electrode\$1) and piezoelectric	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/17 10:21

-	133	capacitor same barrier same perovskite	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/17 13:53
-	2	("6545392").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/17 13:55
-	2	("6307305").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/17 13:55
-	2	("6225877").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/17 13:57
-	274	piezoelectric adj membrane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/17 13:58
-	142	(piezoelectric adj membrane) and electrode\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/17 13:58
-	29	((piezoelectric adj membrane) and electrode\$1) and ((si or silicon or gallium or GAAS) with substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/17 13:59